

Silicon NPN Power Transistors

2SC3486

DESCRIPTION

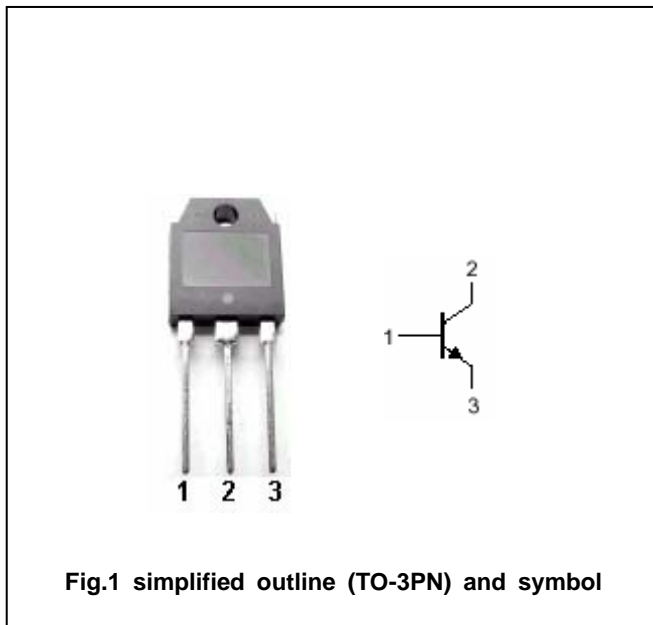
- With TO-3PN package
- High voltage ,high speed
- Wide area of safe operation

APPLICATIONS

- For color TV display horizontal output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		6	A
I _{CM}	Collector current-peak		16	A
P _C	Collector power dissipation	T _C =25	120	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA ; R _{BE} =	800			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =5mA ; I _E =0	1500			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =5mA ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =1.2A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A; I _B =1.2A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1	mA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	8			
f _T	Transition frequency	I _C =1A ; V _{CE} =10V		3		MHz
Switching times						
t _{stg}	Storage time	I _C =5A; R _L =40 I _{B1} =1A; I _{B2} =-2A			3.0	μs
t _f	Fall time				0.3	μs

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PACKAGE OUTLINE

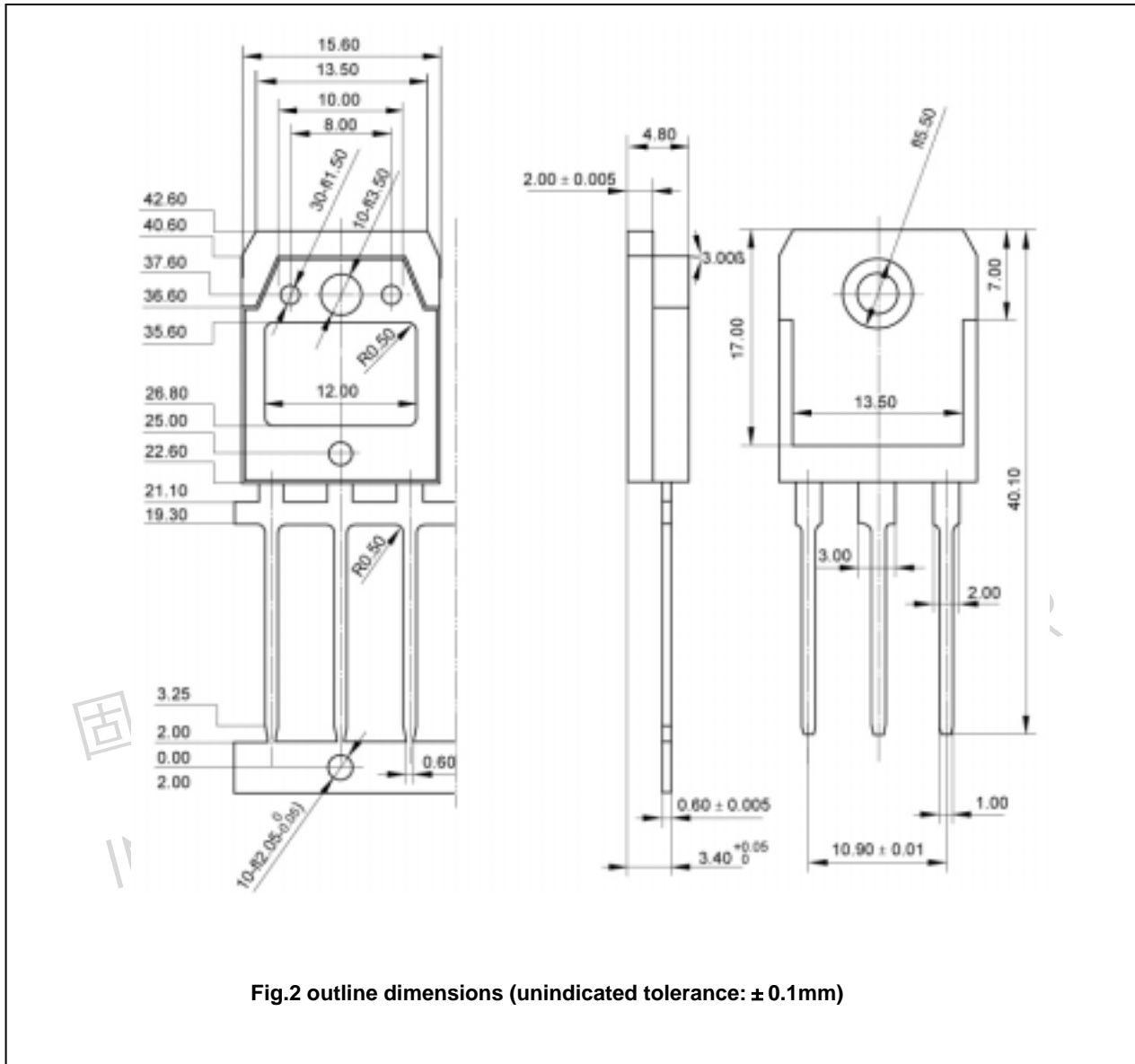


Fig.2 outline dimensions (unindicated tolerance: ± 0.1mm)